

FOR IMMEDIATE RELEASE

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Product Inquiries:

High Frequency & Optical Semiconductor
Global Marketing Department B
Tel +81-3-3218-3014
Sato.Kazuhiko@aj.MitsubishiElectric.co.jp
<http://www.mitsubishichips.com/>

Media Contact:

Public Relations Division
Mitsubishi Electric Corporation
Tel: +81-3-3218-3380
prd.gnews@nk.MitsubishiElectric.co.jp
<http://global.mitsubishielectric.com/news/>

MITSUBISHI ELECTRIC ANNOUNCES SALE OF ‘MGF4935AM’ Ku BAND LOW NOISE GaAs HEMT

Tokyo, May 20, 2008 – Mitsubishi Electric Corporation (President and CEO: Setsuhiro Shimomura) announced today it has developed a full-mold package low noise Ku¹ band GaAs High Electron Mobility Transistor (HEMT), the MGF4935AM, highly suitable for low noise amplifiers in Direct Broadcast Satellite (DBS) reception systems and Very Small Aperture Terminal (VSAT) systems. Shipment will begin on May 26, 2008.

1: Downlink: 12GHz, Uplink: 14GHz

Sale Summary

Product	Model	Features	Sample price	Shipment date	Production
Low Noise GaAs HEMT	MGF4935AM ²	NF: 0.45dB Gs: 12.0dB (f=12GHz)	25 yen	May 26, 2008	4 million / month

2: Suitable for use in first stage of low noise amplifiers for DBS

Aim of Sale

Satellite communication systems can build a much larger service area network in a short time compared to fiber optic cable communication systems or other communication systems. They are expected to be quickly adopted by countries like China, which is experiencing rapid economic growth.

At the same time, when it comes to satellite antennae, a reception converter that receives Ku band waves from satellites converts them into 1-2GHz to send them to the signal processing circuit; HEMTs are used in low noise amplifiers for reception converters, and the increase in satellite communication systems is creating a larger demand for these transistors.

Mitsubishi Electric has developed a full-mold package HEMT with the lowest noise characteristics in the industry. Full-mold package HEMT is lower-priced compared to other types of HEMTs, and it improves cost performance in satellite communication equipment by using this product in the first stage of amplifiers, which strictly requires low noise characteristics.

Product Features

1) Lowest noise characteristics in full-mold package, suitable for use in the first stage of amplifiers

By improving chip performances and by optimizing package structure, the noise figure (NF) has been improved by 0.05dB to 0.45dB, compared to our previous model (full-mold package MGF4934BM). This improvement allows this product to be used in the first stage of amplifiers, which requires low noise characteristics. The full-mold package HEMT, available at a lower price than other HEMTs, improves cost performance in satellite communication equipment.

2) An industry standard 4-pin full-mold package, for shorter development periods for satellite communication equipment manufacturers

The MGF4935AM has an industry standard 4-pin full-mold package. An unchanged foot pattern from the previous model will shorten development periods for satellite communication equipment manufacturers.

Future Developments

Mitsubishi Electric will increase its lineup of full-mold packaged low noise GaAs HEMTs with improvements in gain and noise characteristics.

Features

- Recommended bias condition: $V_{DS}=2V$, $I_D=10mA$
- Noise figure (NFmin.): 0.45dB (f=12GHz, typical)
- Associated gain (Gs): 12.0dB (f=12GHz, typical)

About Mitsubishi Electric

With over 80 years of experience in providing reliable, high-quality products to both corporate clients and general consumers all over the world, Mitsubishi Electric Corporation (TSE:6503) is a recognized world leader in the manufacture, marketing and sales of electrical and electronic equipment used in information processing and communications, space development and satellite communications, consumer electronics, industrial technology, energy, transportation and building equipment. The company recorded consolidated group sales of 4,049.8 billion yen (US\$ 40.5 billion*) in the fiscal year ended March 31, 2008. For more information visit <http://global.mitsubishielectric.com>

*At an exchange rate of 100 yen to the US dollar, the rate given by the Tokyo Foreign Exchange Market on March 31, 2008

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